产品概览

NVBG015N065SC1: Silicon Carbide MOSFET, N-Channel, 650V, 12 mΩ ， D2PAK-7L

欲看完整文档，请参阅数据表。

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

特性

- Qualified for Automotive According to AEC-Q101
- 650V rated
- Max RDS(on) = 18 mΩ at Vgs = 18V, Id = 75A
- High Speed Switching and Low Capacitance
- 100% UIL Tested
- Devices are RoHS Compliant

优势

- Automotive Grade

应用

- Automotive DC/DC
- Automotive PFC

终端产品

- Automotive On Board Charger
- Automotive DC/DC converter for EV/PHEV

器件电气规格

产品	Pricing ($/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV_{DSS} (V)	$I_{D(max)}$ (A)	$R_{DS(on)}$ Typ @ 25°C (mΩ)	Q_g Total (C)	Output Capacitance (C)	T_j Max (°C)	Package Type
NVBG015N065SC1	17.4357	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	650	145	12	283	424	175	D2PAK7 (TO-263-7L HV)

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn 。

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